

Form PTO 1449  U.S. Department of Commerce Patent and Trademark Office  Information Disclosure Statement by Applicant	ATTY. DOCKET NUMBER NITT.0194	SERIAL NUMBER <del>To be Assigned</del> 10782997
	APPLICANT TSUCHIYA et al.	
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**U.S. Patent Documents**

Examiner Initial	DOCUMENT NUMBER	DATE	NAME	CLA SS	SUBC CLASS	FILING DATE

**Foreign Patent Documents**

Examiner Initial	DOCUMENT NUMBER	FILING DATE	COUNTRY	CLASS	SUB- CLASS	TRANSLATION	
						YES	No
ms	10-84170	8/11/97	Japan			Abstract	X

**Other Documents (Including Author, Title, Date Pertinent Pages, Etc.)**

ms	R. Bhat et al., "High-Performance 1.3 $\mu\text{m}$ AlGaInAs/InP Strained Quantum Well Lasers Grown by Organometallic Chemical Vapor Deposition", Journal of Crystal Growth (1004), pp. 858-865
	P.J.A. Thijs et al., "High Performance Buried Heterostructure $\lambda=1.5 \mu\text{m}$ InGaAs/AlGaInAs Strained-Layer Quantum Well Laser Diodes", 10 <sup>th</sup> International Conference on Indium Phosphide and Related Materials (1996) ThA2-2, pp. 765-768
	Tawee Tanbun-Ek et al., "High Performance Buried Heterostructure 1.55 $\mu\text{m}$ Wavelength AlGaInAs/InP Multiple Quantum Well Lasers Grown Entirely by NOVPE Technique", 10 <sup>th</sup> International Conference on Indium Phosphide and Related Materials (May 1998) ThP-48, pp. 702-705
ms	C. E. Zah et al., "High-Temperature Modulation Dynamics of 1.3 $\mu\text{m}$ Al <sub>x</sub> Ga <sub>1-x</sub> As/InP Compressive-Strained Multiple-Quantum-Well Lasers", 14 <sup>th</sup> International Semiconductor Laser Conference (1994), TH 1.3, pp. 215-216

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**EXAMINER:** Initial if citation is considered, whether or not citation is in conformance with MPEP 609; draw a line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant